

Remarks

This amendment is responsive to the Patent Office communication mailed November 1, 2002 which states that the prior response (filed 8/2/02) was not fully responsive to the prior office action, specifically the rejection under Section 112.

It is submitted that the above-referenced amendment to claim 22 renders all of the claims 22-26 of sufficient clarity to satisfy the requirements of Section 112.

The application is now in condition for allowance.

Respectfully Submitted,

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**"Version With Markings To Show Changes"**

- 1) Kindly amend claim 22 as follows:

A method for forming a semiconductor structure, comprising:

depositing a first insulative layer over a semiconductor layer;

forming a lower level of interconnect members over the first insulative layer;

depositing a second insulative layer between and over the lower level of  
interconnect members;

forming an upper level of interconnect members over the second insulative  
layer

removing portions of the second insulative layer positioned between  
interconnect members of the lower and upper levels; and

forming a third insulative layer in regions from which the second insulative  
layer is removed.